

SB521BZ-30

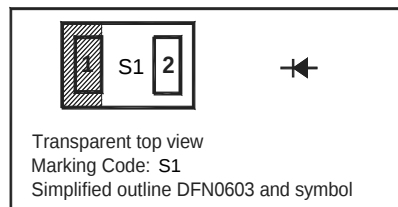
Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Low V_F
- High Reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

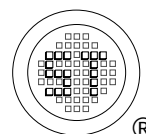


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

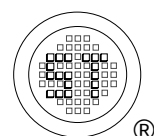
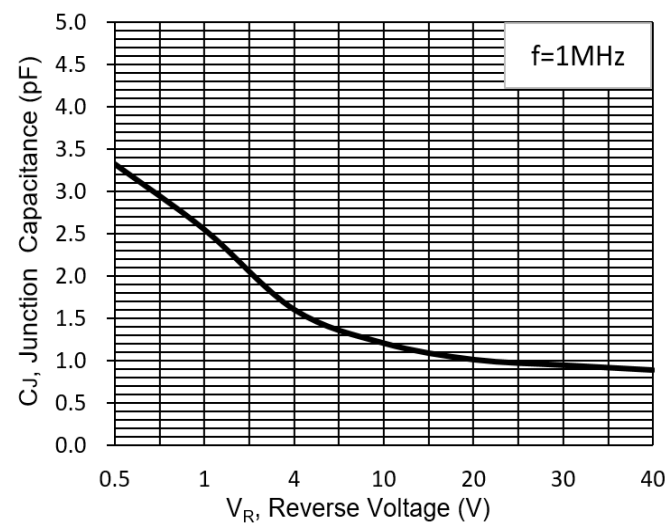
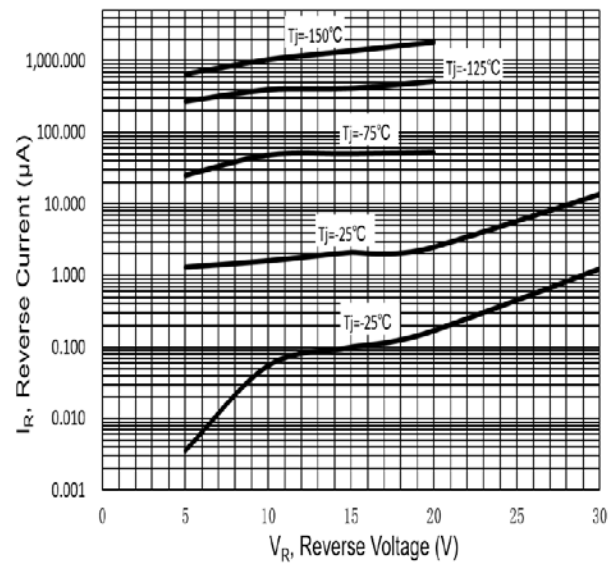
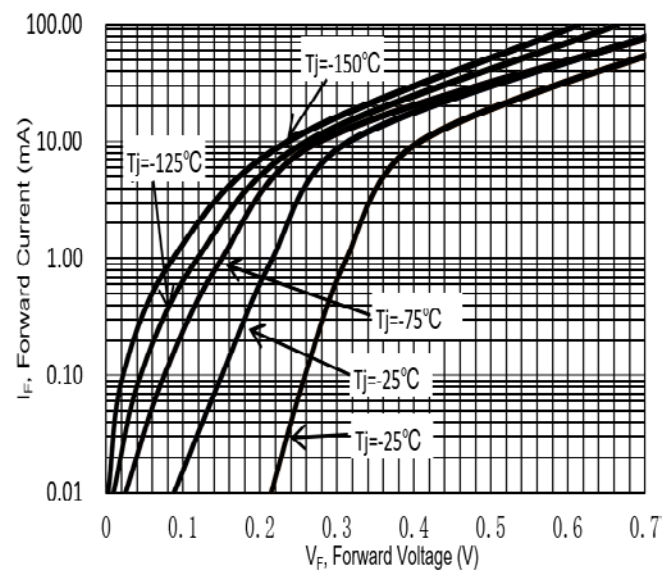
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average rectified forward current	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (8.3 ms)	I_{FSM}	500	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.37	V
Reverse Current at $V_R = 10\text{ V}$	I_R	7	μA



Electrical Characteristics Curves

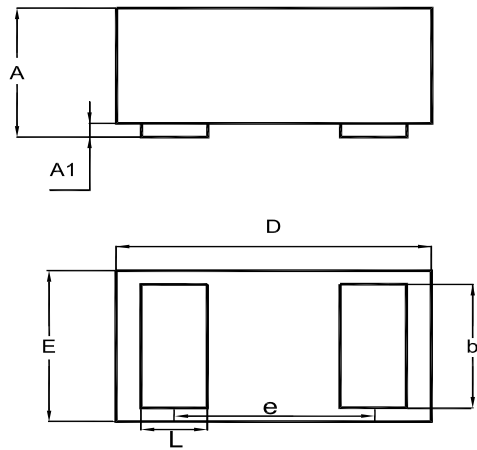


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PACKAGE OUTLINE

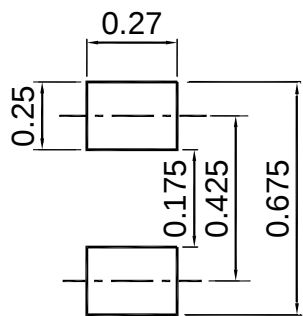
Plastic surface mounted package; 2 leads

DFN0603



UNIT	A	A1	b	D	E	e	L
mm	0.27 0.33	0 0.025	0.21 0.29	0.57 0.65	0.28 0.35	0.355	0.14 0.22

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN0603	8	2 ± 0.05	0.78 ± 0.002	178	7	10,000

Marking information

"S1" = Part No.
Font type: Arial

